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High performance multi-channel MOSFET on InGaAs for RF amplifiers

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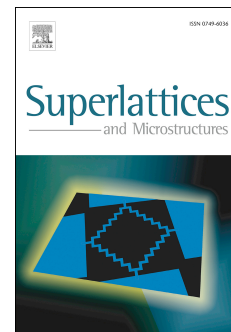
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for RF Amplifiers**

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